

**TYPE  
NAME**

**ML60116R , ML64116R**

**DESCRIPTION**

ML6XX16 is a high power AlGaAs semiconductor laser which provides a stable, single transverse mode oscillation with emission wavelength of 785nm and standard light output of 30mW.

ML6XX16 is produced by the MOCVD crystal growth method which is excellent in mass production and characteristics uniformity. This is a high -performance, highly reliable, and long life semiconductor laser.

**FEATURES**

- Output 30mW (CW) 40mW (pulse)
- Short astigmatic distance
- MQW \* active layer  
     \*: Multiple Quantum Well
- Built-in monitor photodiode

**APPLICATION**

Optical disc drive ( rewritable , write once)

**ABSOLUTE MAXIMUM RATINGS** (Note 1)

Symbol	Parameter	Conditions	Ratings	Unit
Po	Light output power	CW	<b>40</b>	mW
		Pulse(Note 2)	<b>50</b>	
VRL	Reverse voltage (laser diode)	-	<b>2</b>	V
VRD	Reverse voltage (Photodiode)	-	<b>30</b>	V
IFD	Forward current (Photodiode)	-	<b>10</b>	mA
Tc	Case temperature	-	<b>-40 ~ +60</b>	°C
Tstg	Storage temperature	-	<b>-55 ~ +100</b>	°C

Note1: The maximum rating means the limitation over which the laser should not be operated even instant time, and this does not mean the guarantee of its lifetime.As for the reliability,please refer to the reliability report from Mitsubishi Semiconductor Quality Assurance Department.

Note2: TARGET SPEC /Condition Duty less than 50%,pulse width less than 1ms

**ELECTRICAL/OPTICAL CHARACTERISTICS** (Case temperature Tc=25°C)

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
Ith	Threshold current	CW	-	<b>30</b>	<b>50</b>	mA
Iop	Operation current	CW,Po=30mW	-	<b>80</b>	<b>110</b>	mA
η	Slope efficiency	CW,Po=30mW	<b>0.40</b>	<b>0.55</b>	<b>0.75</b>	mW/mA
Vop	Operating voltage	CW,Po=30mW		<b>2.0</b>	<b>2.5</b>	V
λp	Peak wavelength	CW,Po=30mW	<b>770</b>	<b>785</b>	<b>800</b>	nm
θ//	Beam divergence angle (parallel)	CW,Po=30mW	<b>8</b>	<b>10</b>	<b>13</b>	°
θ⊥	Beam divergence angle (perpendicular)	CW,Po=30mW	<b>22</b>	<b>25</b>	<b>28</b>	°
Im	Monitoring output current (Photodiode)	CW,Po=30mW,VRD=1V RL=10Ω (Note 4)	-	<b>0.2</b>	-	mA
Im(Note 3)			-	<b>0.5</b>	-	
ID	Dark current (Photodiode)	VRD=10V	-	-	<b>0.5</b>	uA
Ct	Capacitance (Photodiode)	VRD=5V	-	<b>7</b>	-	pF

Note 3: Applicable to ML64116R

Note 4: RL=the load resistance of photodiode

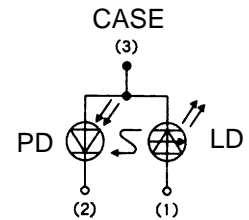
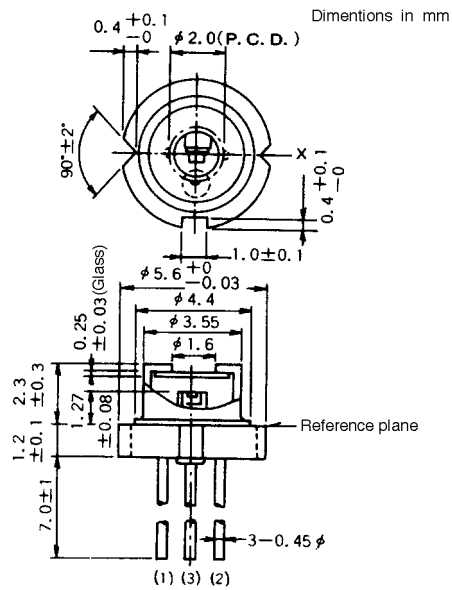
MITSUBISHI LASER DIODES

# ML6XX16 SERIES

FOR OPTICAL INFORMATION SYSTEMS

## OUTLINE DRAWINGS

**ML60116R**



**ML64116R**

